1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection in a leadless ultra small DSN1006-2 (SOD993) Surface-Mounted Device (SMD) package.

2. Features and benefits

Average forward current: I_{F(AV)} ≤ 1 A

Reverse voltage: V_R ≤ 40 V

Low forward voltage, typical: $V_F = 435 \text{ mV}$ Low reverse current, typical: $I_R = 325 \mu A$

Package height typ. 270 μm

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Low power consumption applications
- Ultra high-speed switching
- · LED backlight for mobile application

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|-------------------------|---|-----|-----|------|------|
| I _{F(AV)} | average forward current | δ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 145 °C; square wave | - | - | 1 | А |
| V_R | reverse voltage | T _j = 25 °C | - | - | 40 | V |
| V _F | forward voltage | $I_F = 1 \text{ A}; t_p \le 300 \mu\text{s}; \delta \le 0.02 ;$ $T_j = 25 ^{\circ}\text{C}$ | - | 435 | 505 | mV |
| I _R | reverse current | $V_R = 20 \text{ V; } t_p \le 3 \text{ ms; } \delta \le 0.3 \text{ ;}$ $T_j = 25 \text{ °C}$ | - | 30 | 115 | μΑ |
| | | $V_R = 40 \text{ V; } t_p \le 3 \text{ ms; } \delta \le 0.3 \text{ ;}$ $T_j = 25 \text{ °C}$ | - | 325 | 1250 | μΑ |





Pinning information

Table 2. **Pinning information**

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--|----------------|
| 1 | K | cathode[1] | | 1 - 2 |
| 2 | A | anode | 1 2 | sym001 |
| | | | Transparent top view DSN1006-2 (SOD993) | |

^[1] The marking bar indicates the cathode.

Ordering information

Table 3. **Ordering information**

| Type number | Package | | | | |
|--------------|-----------|--|---------|--|--|
| | Name | Description | Version | | |
| PMEG4010AESB | DSN1006-2 | DSN1006-2, leadless ultra small package; 2 terminals; body 1.0 x 0.6 x 0.27 mm | SOD993 | | |

Marking

Marking codes Table 4.

| Type number | Marking code |
|--------------|--------------|
| PMEG4010AESB | 4A |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|--------------------|-------------------------------------|---|-----|-----|-------|------|
| V_R | reverse voltage | T _j = 25 °C | | - | 40 | V |
| I _F | forward current | T _{sp} ≤ 140 °C; δ = 1 | | - | 1.4 | Α |
| I _{F(AV)} | average forward current | $\bar{\delta}$ = 0.5 ; f = 20 kHz; $T_{amb} \leq$ 115 °C; square wave | [1] | - | 1 | A |
| | | δ = 0.5 ; f = 20 kHz; $T_{sp} \le$ 145 °C; square wave | | - | 1 | A |
| I _{FRM} | repetitive peak forward current | $t_p \le 1 \text{ ms}; \delta \le 0.25$ | | - | 4 | Α |
| I _{FSM} | non-repetitive peak forward current | t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave | | - | 10 | A |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [2] | - | 0.525 | W |
| | | | [3] | - | 1 | W |
| | | | [1] | - | 1.78 | W |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm² each.

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--|--|-------------|--------|-----|-----|-----|------|
| R _{th(j-a)} thermal resistance from junction to ambient | | in free air | [1][2] | - | - | 240 | K/W |
| | | [1][3] | - | - | 125 | K/W | |
| | ambient | | [1][4] | - | - | 70 | K/W |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | | [5] | - | - | 15 | K/W |

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm² each.
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of anode tab.

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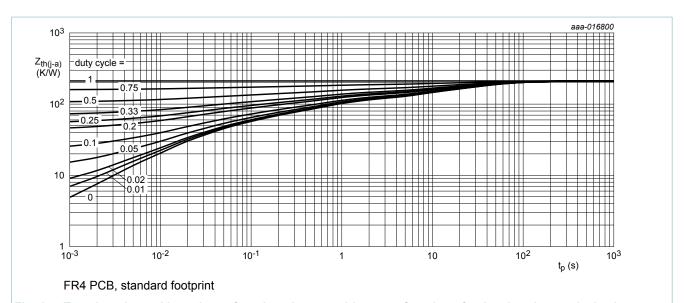
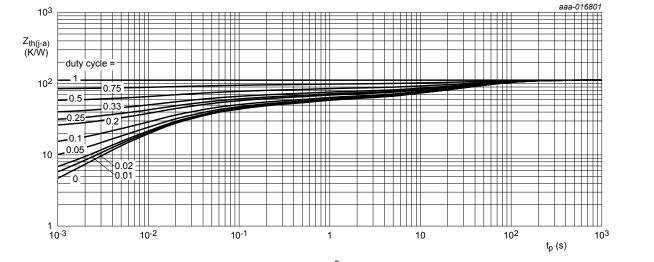


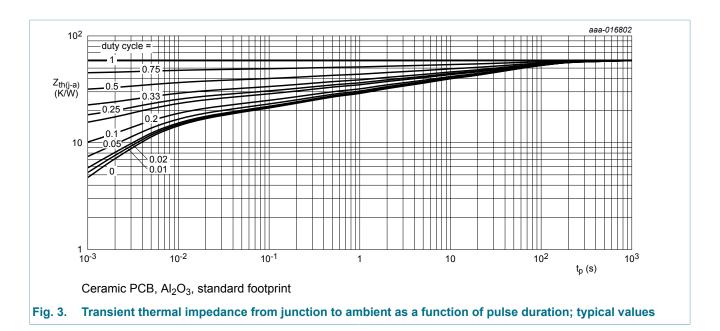
Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for anode and cathode 1 cm² each

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

Product data sheet



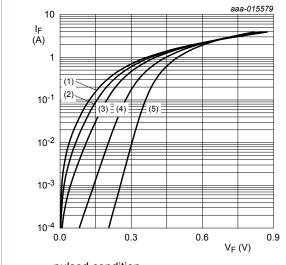
10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------------------|---|--|-------|--------------|----------------|------------------|
| $V_{(BR)R}$ | reverse breakdown voltage | $I_R = 10 \text{ mA}; t_p = 300 \mu\text{s}; \delta = 0.02 ;$ $T_j = 25 ^{\circ}\text{C}$ | 40 | - | - | V |
| V _F forward voltage | forward voltage | I_F = 1 mA; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C | - | 145 | - | mV |
| | | I_F = 10 mA; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_j = 25 °C | - | 205 | - | mV |
| | $I_F = 100 \text{ mA; } t_p \le 300 \mu \text{s; } \delta \le 0.02 \text{ ; }$ $T_j = 25 \text{ °C}$ $I_F = 200 \text{ mA; } t_p \le 300 \mu \text{s; } \delta \le 0.02 \text{ ; }$ $T_j = 25 \text{ °C}$ | · · | - | 275 | 330 | mV |
| | | · | - | 305 | - | mV |
| | | $I_F = 500 \text{ mA}; t_p \le 300 \mu\text{s}; \delta \le 0.02 ;$ $T_j = 25 ^{\circ}\text{C}$ | - | 365 | 425 | mV |
| | | I_F = 700 mA; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_j = 25 °C | - | 395 | - | mV |
| | | I_F = 1 A; t_p ≤ 300 μs; δ ≤ 0.02 ; T_j = 25 °C | - | 435 | 505 | mV |
| I _R | reverse current | $V_R = 5 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3 ; T_j = 25 \text{ °C}$ | - | 10 | - | μA |
| | | $V_R = 10 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3 ;$ $T_j = 25 \text{ °C}$ | - | 15 | 60 | μA |
| | | V_R = 20 V; $t_p \le 3$ ms; $\delta \le 0.3$; T_j = 25 °C | - | 30 | 115 | μA |
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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-----------------------|---|-----|-----|------|------|
| | | $V_R = 40 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3 ;$ $T_j = 25 \text{ °C}$ | - | 325 | 1250 | μA |
| C _d | diode capacitance | V _R = 1 V; f = 1 MHz; T _j = 25 °C | - | 75 | - | pF |
| | | V _R = 10 V; f = 1 MHz; T _j = 25 °C | - | 22 | - | pF |
| t _{rr} | reverse recovery time | $I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$ | - | 3.1 | - | ns |



pulsed condition

(1)
$$T_i = 150 \, ^{\circ}C$$

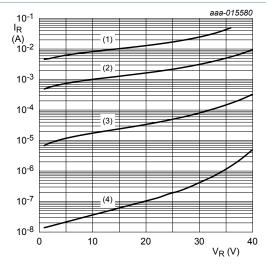
(2)
$$T_i = 125 \, ^{\circ}C$$

(3)
$$T_i = 85 \, ^{\circ}C$$

(4)
$$T_j = 25 \,^{\circ}C$$

(5) T_j = −40 °C

Fig. 4. Forward current as a function of forward voltage; typical values



pulsed condition

(1)
$$T_i = 125 \, ^{\circ}C$$

(2)
$$T_i = 85 \, ^{\circ}C$$

(3)
$$T_i = 25 \, ^{\circ}C$$

(4)
$$T_j = -40 \, ^{\circ}\text{C}$$

Fig. 5. Reverse current as a function of reverse voltage; typical values

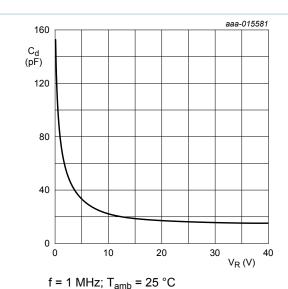
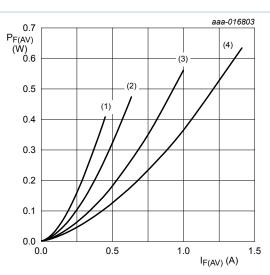


Fig. 6. Diode capacitance as a function of reverse voltage; typical values



 $T_j = 150 \,^{\circ}\text{C}$

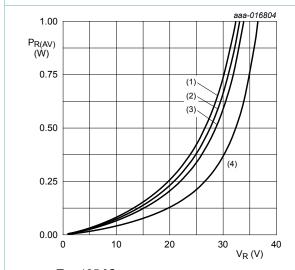
 $(1) \delta = 0.1$

(2) $\delta = 0.2$

 $(3) \delta = 0.5$

 $(4) \delta = 1$

Fig. 7. Average forward power dissipation as a function of average forward current; typical values



T_j = 125 °C

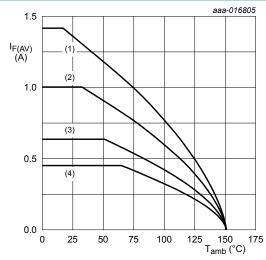
 $(1) \delta = 1$

 $(2) \delta = 0.9$

 $(3) \delta = 0.8$

 $(4) \delta = 0.5$

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T_i = 150 °C

(1) δ = 1; DC

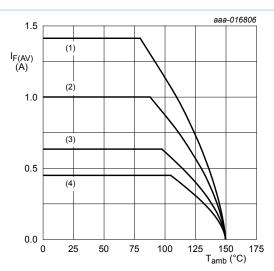
(2) $\delta = 0.5$; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 9. Average forward current as a function of ambient temperature; typical values

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FR4 PCB, mounting pad for anode and cathode 1 cm² each

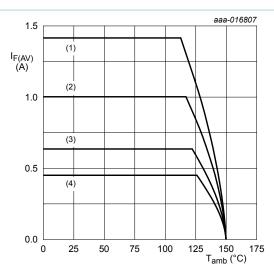
T_i = 150 °C

(1) δ = 1; DC (2) δ = 0.5; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

 $T_i = 150 \,{}^{\circ}\text{C}$

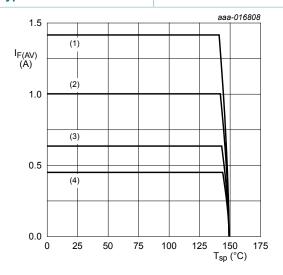
(1) $\delta = 1$ (DC)

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



T_i = 150 °C

(1) δ = 1 (DC)

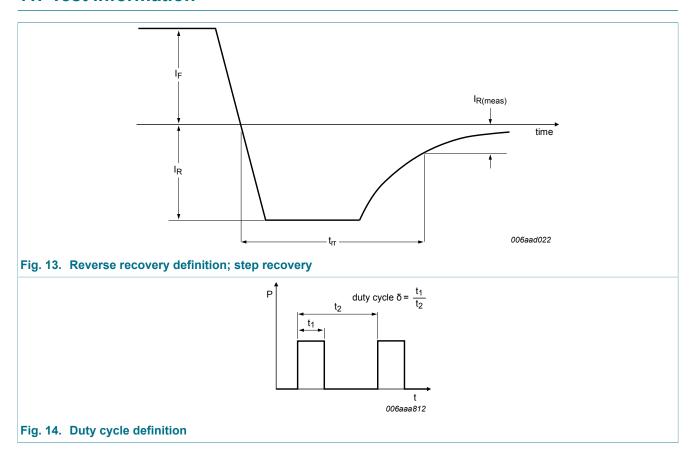
(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

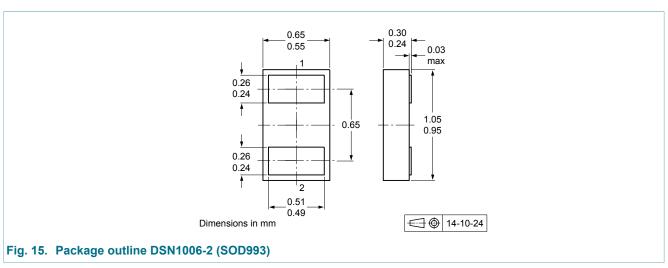
Fig. 12. Average forward current as a function of solder point temperature; typical values

11. Test information



The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

12. Package outline

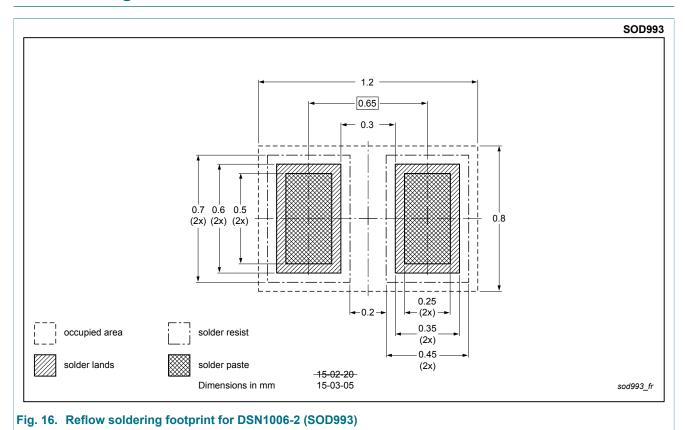


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13. Soldering



14. Mounting

SOD993 is an ultra small Discretes Silicon No-leads (DSN) package allowing maximized utilization of the package area for active silicon. Due to the special product design, NXP investigated the board assembly process parameters. In order to have an optimum soldering quality, NXP advises following the assembly recommendations explained in AN11689.

15. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|------------------|---------------------|------------------------|---------------|------------------|
| PMEG4010AESB v.3 | 20151006 | Product data sheet | - | PMEG4010AESB v.2 |
| Modifications: | Changed status to " | Product data sheet" | | |
| PMEG4010AESB v.2 | 20150430 | Preliminary data sheet | - | PMEG4010AESB v.1 |
| PMEG4010AESB v.1 | 20141128 | Objective data sheet | - | - |

16. Legal information

16.1 Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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